

Sample Parameter	Analysis Parameter	Sputter Parameter	
Sample:	PI: Ga	PI: Cs	
Origin:	Energy: 25 keV	Energy: Unknown	
Polarity: negative	Current: Unknown	Current: Unknown	
File: RT37.tfd	Area: 99.6x99.6 $\mu\text{m}^2$	Area: 250.1x250.1 $\mu\text{m}^2$	
Comments:			

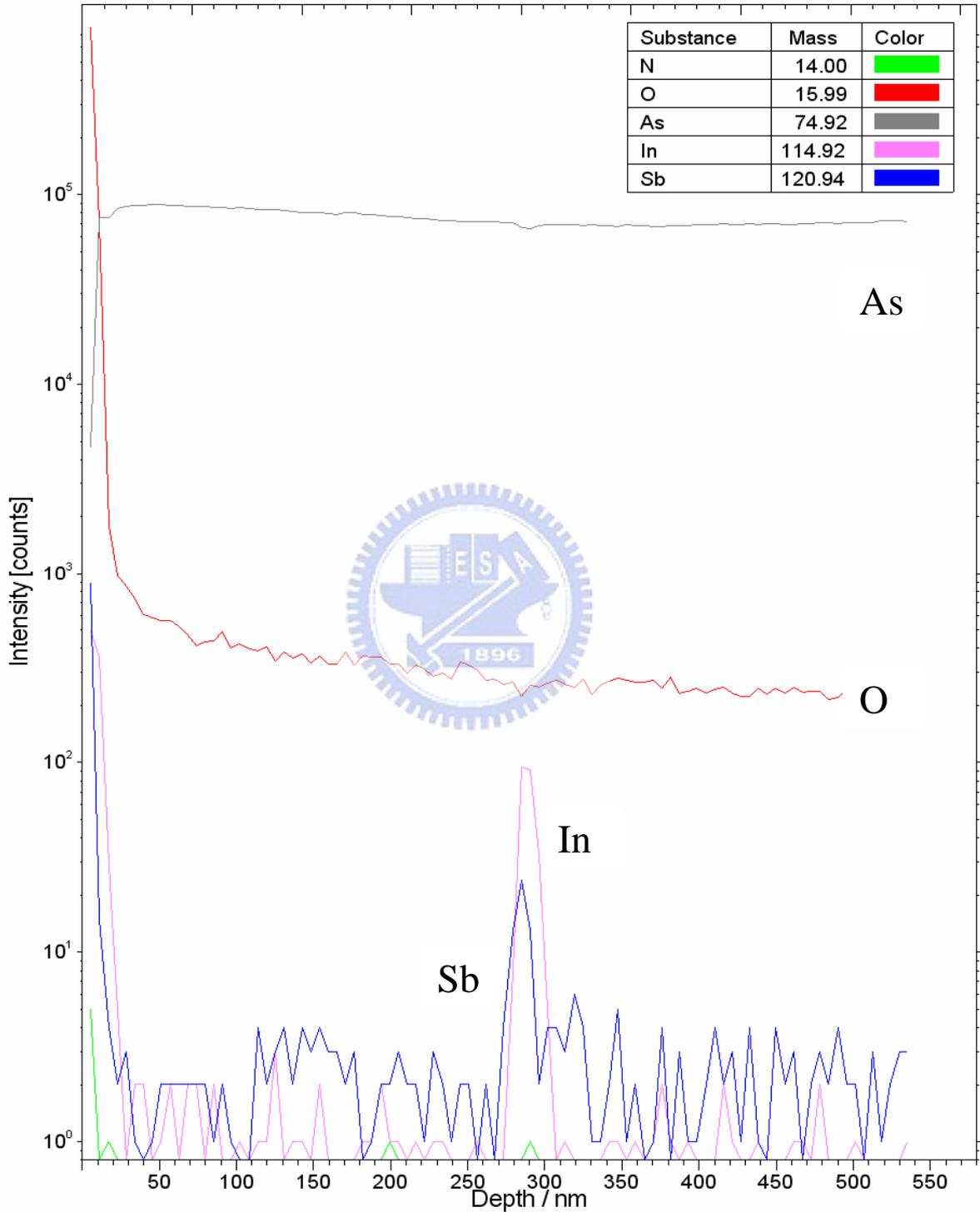


圖 5-1 InAsSb(6)樣品之 SIMS 縱深曲線分析圖

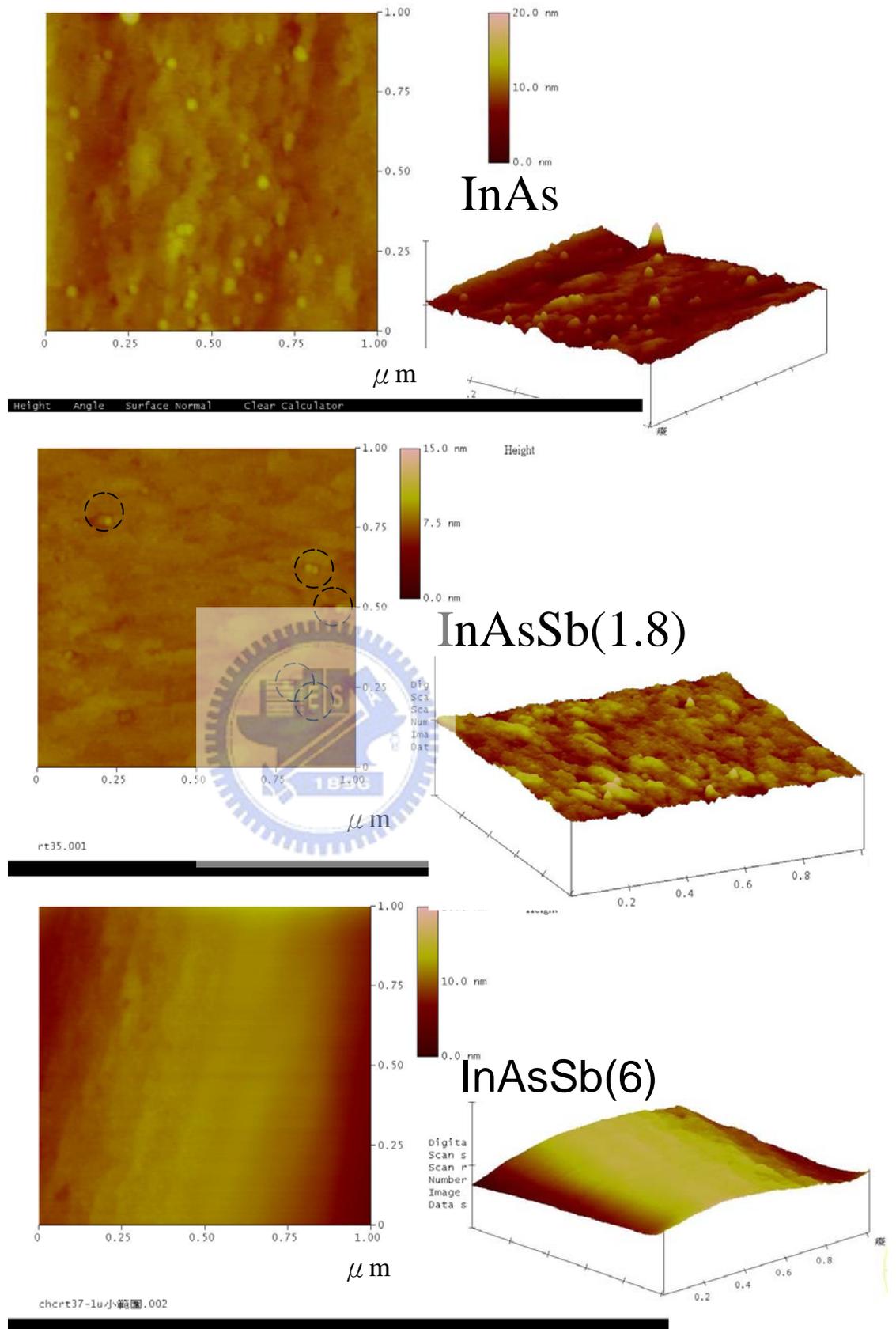


圖 5-2 三片樣品之 AFM 平面圖與立體圖

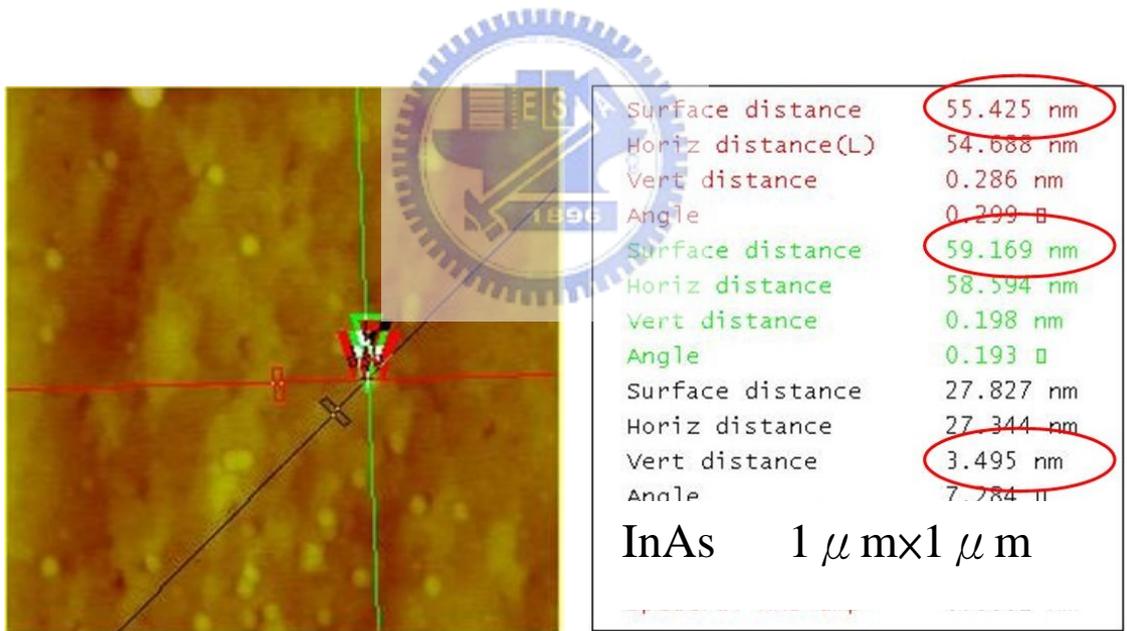
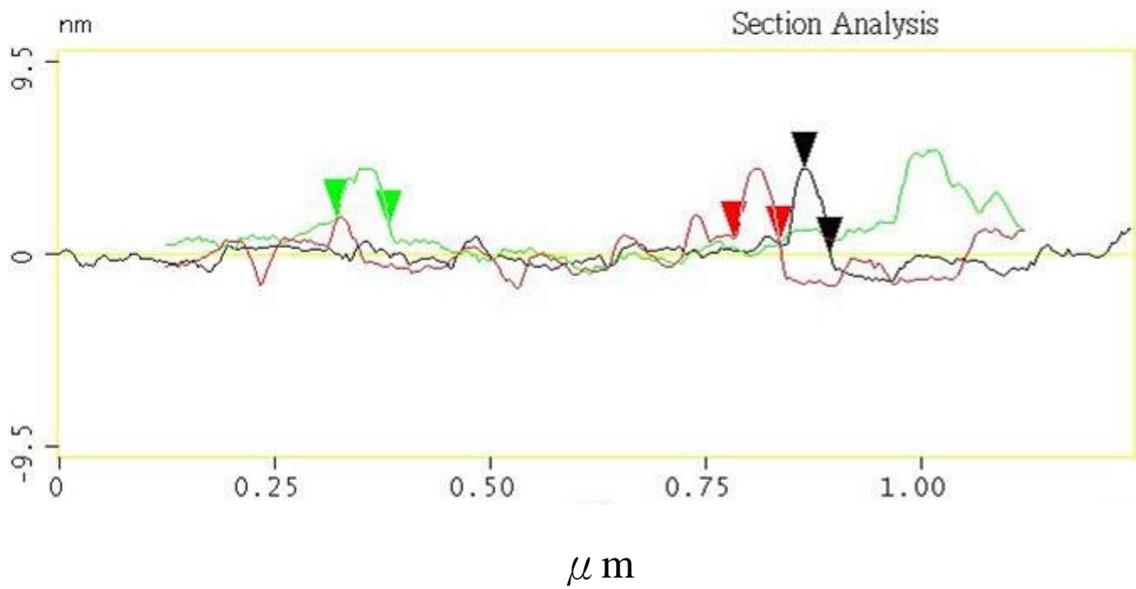
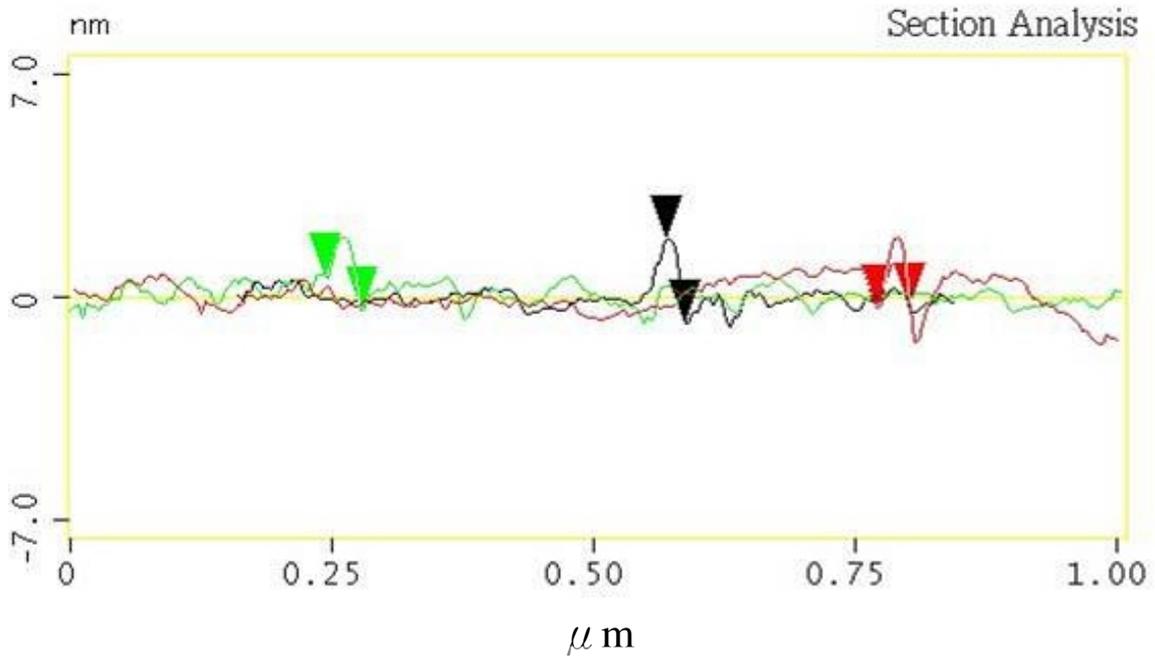


圖 5-3(a) InAs 樣品之 AFM 剖面分析圖



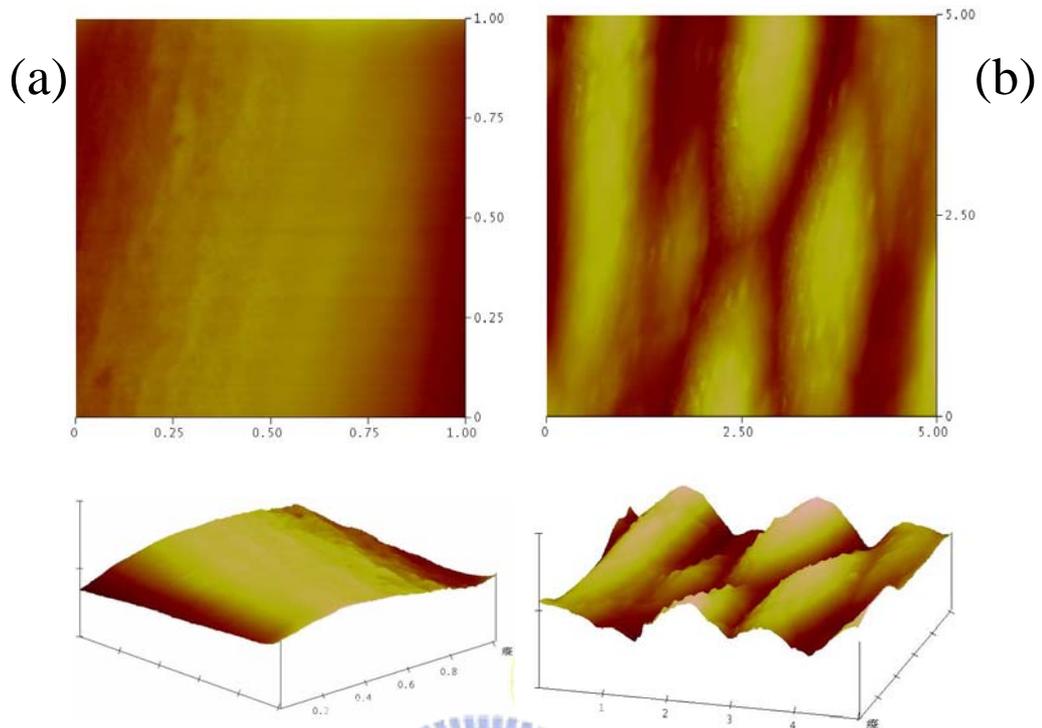
Surface distance	31.677 nm
Horiz distance(L)	31.250 nm
Vert distance	0.178 nm
Angle	0.326 °
Surface distance	35.481 nm
Horiz distance	35.156 nm
Vert distance	1.245 nm
Angle	2.029 °
Surface distance	15.954 nm
Horiz distance	15.625 nm
Vert distance	2.696 nm
Angle	9.789 °

InAsSb(1.8) 1  $\mu$  m $\times$ 1  $\mu$  m

圖 5-3(b) InAsSb(1.8)樣品之 AFM 剖面分析圖

1  $\mu\text{m}$

5  $\mu\text{m}$



(c) 10  $\mu\text{m}$  20  $\mu\text{m}$  (d)

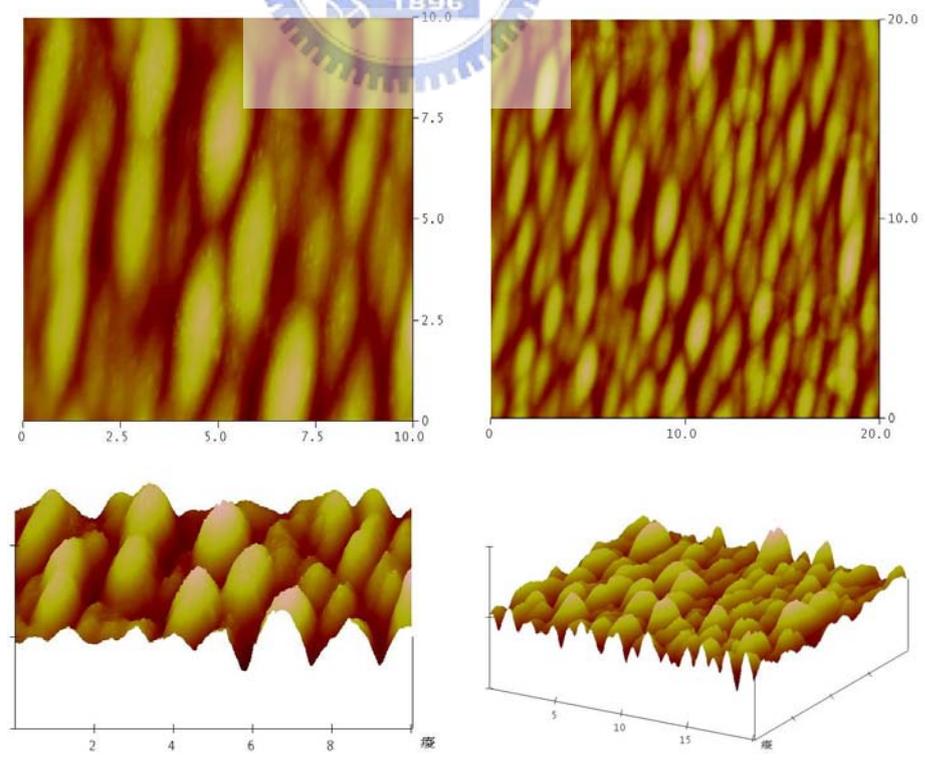
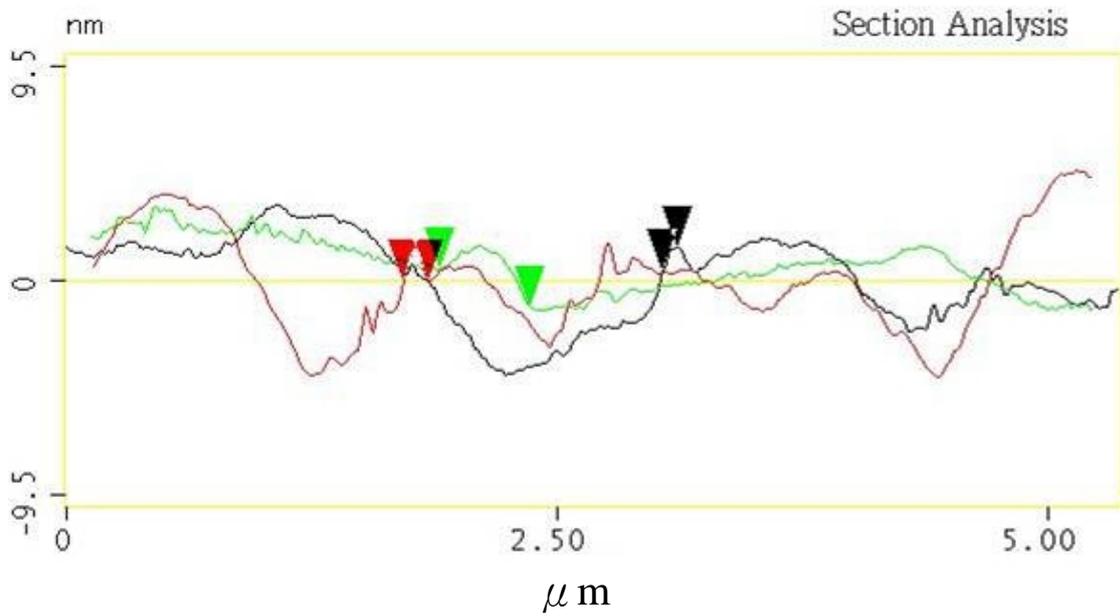


圖 5-4 InAsSb(6)樣品不同尺寸掃描下之 AFM 圖



5  $\mu\text{m} \times 5 \mu\text{m}$

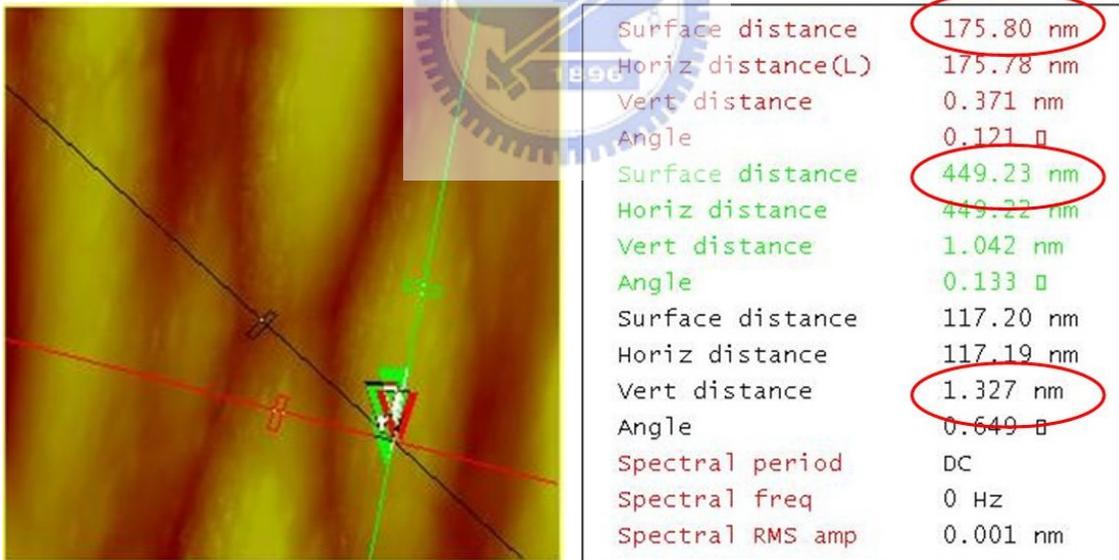


圖 5-5 InAsSb(6)樣品之 AFM 剖面分析圖

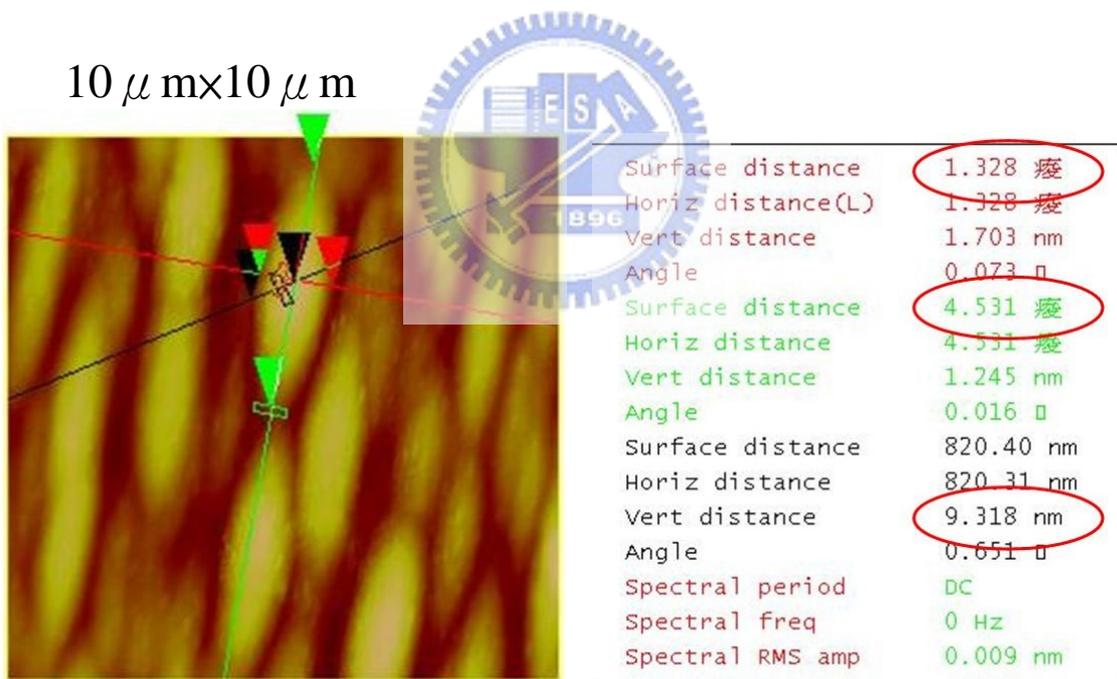
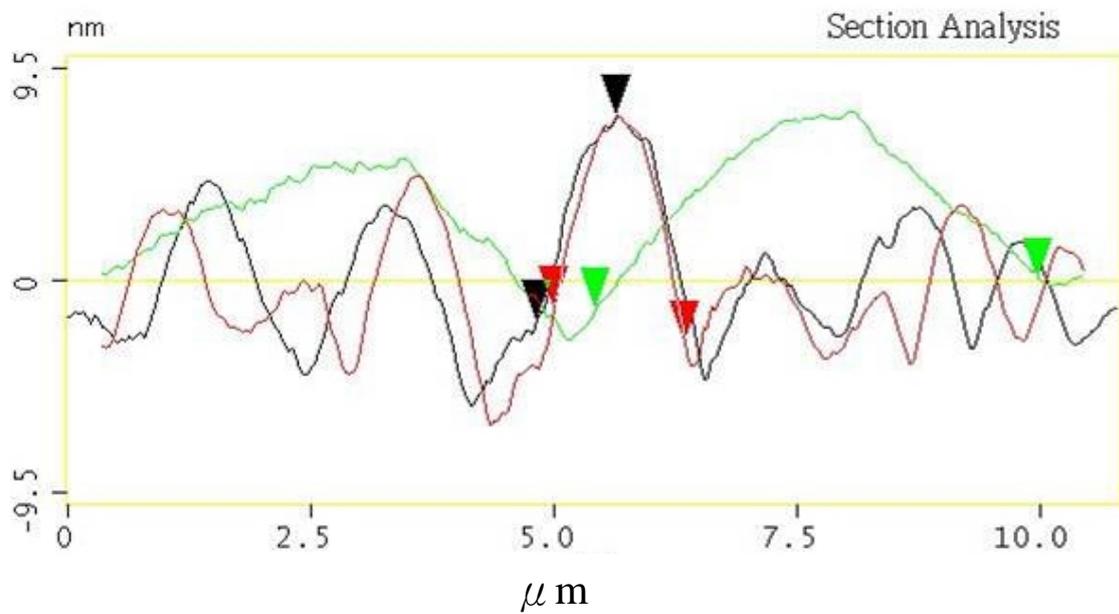


圖 5-6 InAsSb(6)樣品之 AFM 剖面分析圖

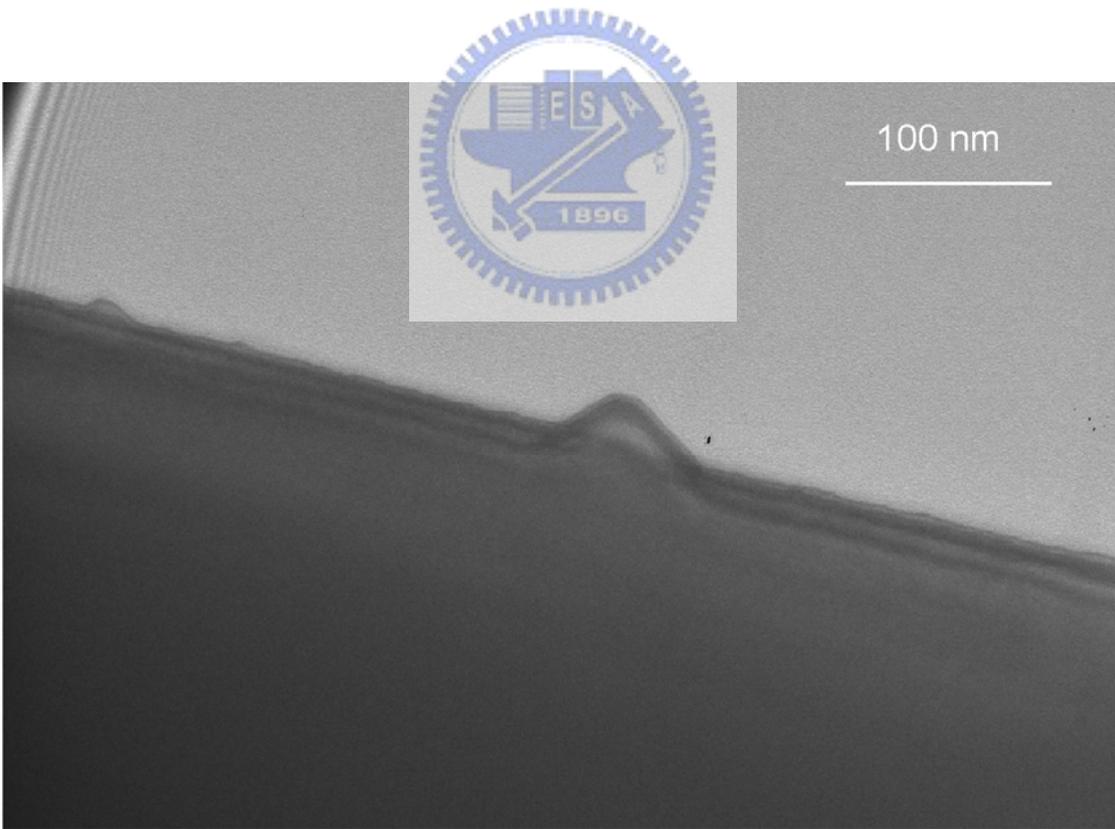
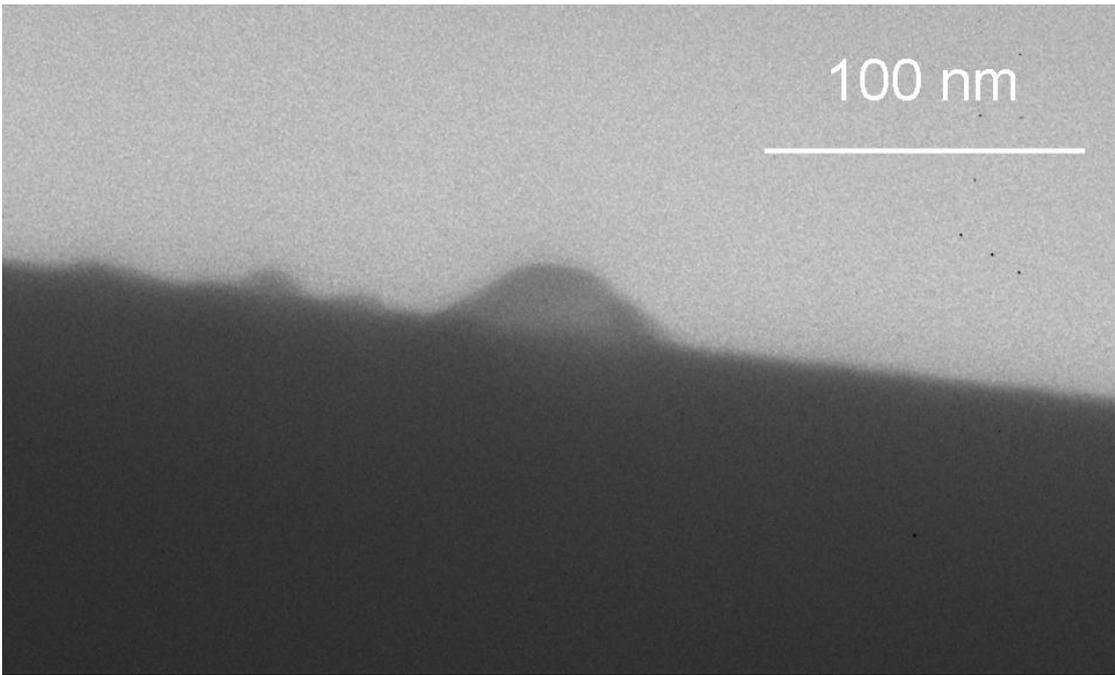


圖 5-7 InAsSb(6)樣品之 TEM 剖面分析圖



圖 5-8 InAsSb(6)樣品之 RHEED patterns